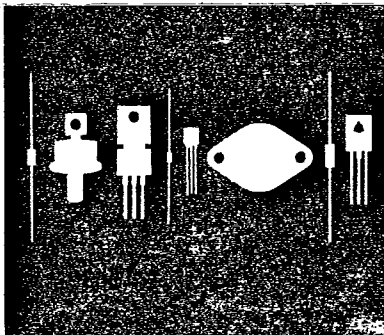


CENTRAL SEMICONDUCTOR

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Central
Semiconductor Corp.
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145 Adams Avenue
Hauppauge, New York 11788



1N5615
1N5617
1N5619
1N5621
1N5623

FAST RECOVERY
GLASS PASSIVATED RECTIFIER
1.0 AMPS, 200-1000 VOLTS
GPR-1A CASE

DESCRIPTION

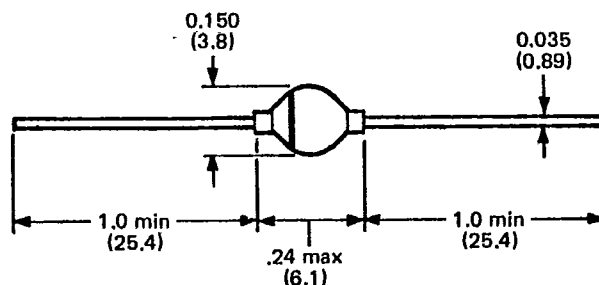
The CENTRAL SEMICONDUCTOR 1N5615 Series types are Silicon Rectifiers mounted in a hermetically sealed, glass passivated package designed for general applications where Fast Reverse Recovery Times and high reliability is desired.

MAXIMUM RATINGS($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	1N5615	1N5617	1N5619	1N5621	1N5623	UNIT
Peak Repetitive Reverse Voltage	V_{RRM}	200	400	600	800	1000	V
DC Blocking Voltage	V_R	200	400	600	800	1000	V
RMS Reverse Voltage	$V_R(\text{RMS})$	140	280	420	560	700	V
Average Forward Current ($T_A=55^\circ\text{C}$)	I_O			1.0			A
Peak Forward Surge Current	I_{FSM}			50			A
Operating and Storage Junction Temperature	T_J, T_{stg}			-65 TO +200			$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I_R	$V_R=\text{Rated } V_{RRM}$		0.5	μA
I_R	$V_R=\text{Rated } V_{RRM}, T_A=100^\circ\text{C}$		25	μA
V_F	$I_F=1.0\text{A}$		1.2	V
BV_R	$I_R=50\mu\text{A}$ (1N5615)	220		V
BV_R	$I_R=50\mu\text{A}$ (1N5617)	440		V
BV_R	$I_R=50\mu\text{A}$, (1N5619)	660		V
BV_R	$I_R=50\mu\text{A}$ (1N5621)	880		V
BV_R	$I_R=50\mu\text{A}$ (1N5623)	1100		V
C	$V_R=12\text{V}, f=130\text{kHz}$		35	pF
t_{rr}	$I_F=0.5\text{A}, I_R=1.0\text{A}, \text{Recov. to } 0.25\text{A}$ (1N5615, 1N5617)		150	ns
t_{rr}	$I_F=0.5\text{A}, I_R=1.0\text{A}, \text{Recov. to } 0.25\text{A}$ (1N5619)		250	ns
t_{rr}	$I_F=0.5\text{A}, I_R=1.0\text{A}, \text{Recov. to } 0.25\text{A}$ (1N5621)		300	ns
t_{rr}	$I_F=0.5\text{A}, I_R=1.0\text{A}, \text{Recov. to } 0.25\text{A}$ (1N5623)		500	ns



DIMENSIONS IN INCHES (MILLIMETERS)